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## N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)(Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)			
40	2 at V <sub>GS</sub> = 10 V	110	120 nC			
40	3.5 at V <sub>GS</sub> = 4.5 V	] 110				

#### **FEATURES**

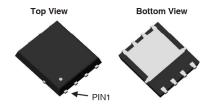
- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested

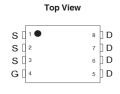


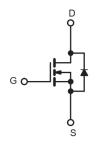
#### **APPLICATIONS**

- DC/DC Converter
- VRM/POL

### **DFN5X6-8L Pin Configuration**







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V <sub>DS</sub>	40	V			
Gate-Source Voltage	V <sub>GS</sub>	± 20	V			
Continuous Dunin Comment (T., 175 °C)	T <sub>C</sub> = 25 °C		110	A		
Continuous Drain Current (T <sub>J</sub> = 175 °C)	T <sub>C</sub> = 100 °C		47.5			
Pulsed Drain Current	I <sub>DM</sub>	400				
Single Avalanche Energy <sup>a</sup>	L = 0.5 mH	E <sub>AS</sub>	485	mJ		
Mayimum Dawar Dissination	T <sub>C</sub> = 25 °C	В	75 <sup>b,c</sup>	W		
Maximum Power Dissipation	T <sub>C</sub> = 100 °C	$ P_D$	36 b,c			
Operating Junction and Storage Temperature F	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	00			
Soldering Recommendations (Peak Temperatur		260	°C			

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) <sup>b,d</sup>	t ≤ 10 s	R <sub>thJA</sub>	17	°C/W		
Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	1.66			

#### Notes:

- a.  $T_C = 25$  °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 10 s
- d. Maximum under steady state conditions is 20  $^{\circ}\text{C/W}.$



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static						•	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$	40			V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1		3	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V			1		
Zero Gate voltage Drain Current		V <sub>DS</sub> = 32 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	— μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	110			Α	
Dunin Common Our Otata Daniatana a	В	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A		2	2.5	0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 30 A		3.5	4	mΩ	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 5 V,I <sub>D</sub> = 30 A		55		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			6480		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		470			
Reverse Transfer Capacitance	C <sub>rss</sub>			445			
Total Gate Charge	Qq			120			
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A		12.5		nC	
Gate-Drain Charge	Q <sub>gd</sub>	1		20			
Gate Resistance	R <sub>g</sub>	f = 1 MHz		0.8		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			8			
Rise Time	t <sub>r</sub>	$V_{DD} = 20 \text{ V, R}_{L} = 1\Omega$		3		ns	
Turn-Off DelayTime	t <sub>d(off)</sub>	$I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1.6 \Omega$		28			
Fall Time	t <sub>f</sub>	1		4			
<b>Drain-Source Body Diode Characterist</b>	tics						
Continous Source-Drain Diode Current	Is	T <sub>C</sub> = 25 °C			110	Α	
Pulse Diode Forward Current (100 μs)	I <sub>SM</sub>				400		
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1 A			1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 30 A, dl/dt = 100 A/μs, T <sub>J</sub> = 25 °C		20		ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	Q <sub>rr</sub>		59		nC	

#### Notes:

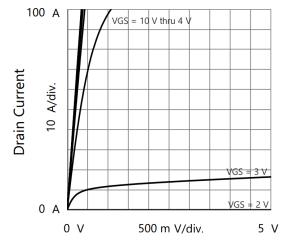
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 

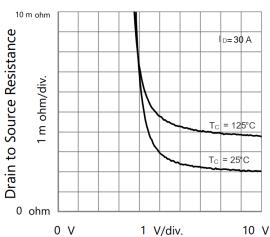
b. Guaranteed by design, not subject to production testing.



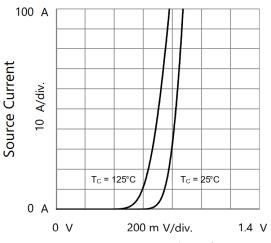
#### **TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



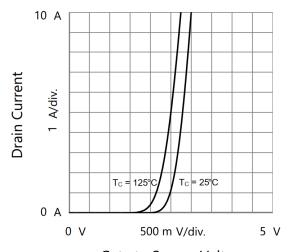
Drain to Source Voltage Output Characteristics



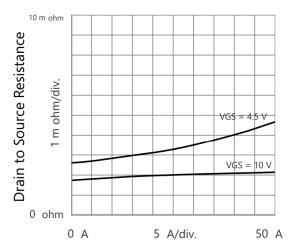
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



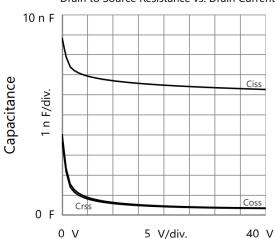
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



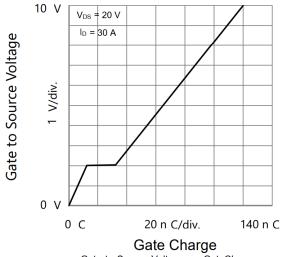
Drain Current
Drain to Source Resistance vs. Drain Current



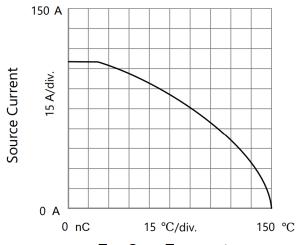
Drain to Source Voltage Capacitances



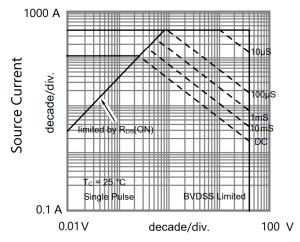
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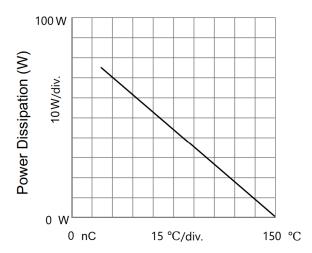
Gate to Source Voltage vs. GateCharge



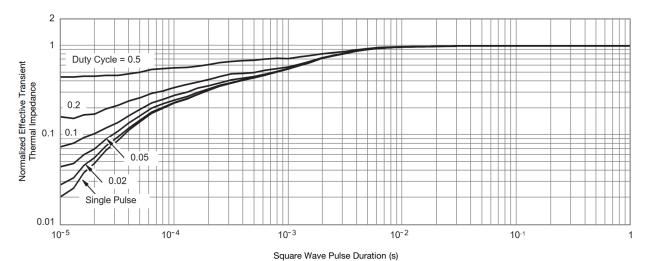
T<sub>C</sub> - Case Temperature



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



T<sub>C</sub> - Case Temperature

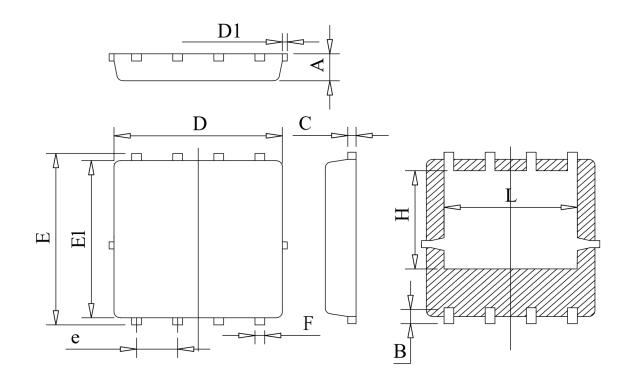


**Normalized Thermal Transient Impedance** 



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## DFN5X6-8L PACKAGE OUTLINE



# COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit: mm

Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25

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